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MBR3035PT MBR3045PT

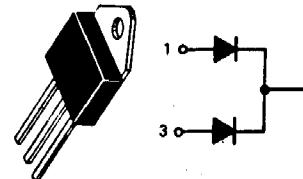
SWITCHMODE POWER RECTIFIERS

...using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — Terminals 1 and 3 May Be Connected For Parallel Operation At Full Rating
- Guardring For Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

30 AMPERES
35 to 45 VOLTS



RATINGS

Rating	Symbol	Maximum	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	35	Volts
Working Peak Reverse Voltage	V_{RWM}	45	
DC Blocking Voltage	V_R		
Average Rectified Forward Current (Rated V_R , $T_C = 105^\circ C$)	$I_{F(AV)}$	30	Amps
Per Device		15	
Peak Repetitive Forward Current, Per Diode (Rated V_R , Square Wave, 20 kHz)	I_{FRM}	30	Amps
Nonrepetitive Peak Surge Current (Surge Applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	200	Amps
Peak Repetitive Reverse Current, Per Diode (2.0 μs , 1.0 kHz) See Figure 6	I_{RRM}	2.0	Amps
Operating Junction Temperature	T_J	-65 to +150	°C
Storage Temperature	T_{Stg}	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	$V/\mu s$

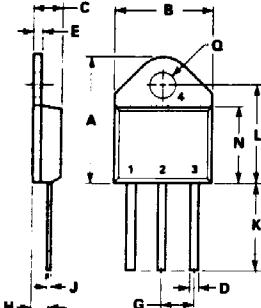
THERMAL CHARACTERISTICS PER DIODE

Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Instantaneous Forward Voltage (1) ($i_F = 20$ Amp, $T_C = 125^\circ C$) ($i_F = 30$ Amp, $T_C = 125^\circ C$) ($i_F = 30$ Amp, $T_C = 25^\circ C$)	V_F	0.60 0.72 0.76	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 125^\circ C$) (Rated dc Voltage, $T_C = 25^\circ C$)	I_R	100 1.0	mA

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	0.830
B	15.49	15.90	0.610	0.626
C	4.19	5.08	0.165	0.200
D	1.02	1.65	0.040	0.065
E	1.35	1.65	0.053	0.065
G	5.21	5.72	0.205	0.225
H	2.65	2.94	0.104	0.116
J	0.38	0.64	0.015	0.025
K	12.70	15.49	0.500	0.610
L	15.88	16.51	0.625	0.650
N	12.19	12.70	0.480	0.500
O	4.04	4.22	0.159	0.166

TO-218AC
PLASTIC



Quality Semi-Conductors